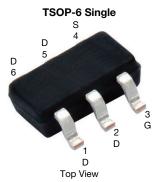
### SQ3419CEV

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**Vishay Siliconix** 

## Automotive P-Channel 40 V (D-S) 175 °C MOSFET



# • TrenchFET<sup>®</sup> power MOSFET

- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>



(3) G O P-Channel MOSFET (4) S

Marking Code: 9L

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	-40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 V$	0.058			
$R_{DS(on)} (\Omega)$ at $V_{GS} = -4.5 V$	0.092			
I <sub>D</sub> (A)	-6.9			
Configuration	Single			

ORDERING INFORMATION	
Package	TSOP-6
Lead (Pb)-free and halogen-free	SQ3419CEV (for detailed order number please see <u>www.vishay.com/doc?79771</u> )

PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-source voltage	V <sub>DS</sub>	-40	V		
Gate-source voltage	V <sub>GS</sub>	± 20	v		
	T <sub>C</sub> = 25 °C	1	-6.9		
Continuous drain current	T <sub>C</sub> = 125 °C	I <sub>D</sub>	-4		
Continuous source current (diode conduction	I <sub>S</sub>	-6.3	А		
Pulsed drain current <sup>a</sup>	I <sub>DM</sub>	-27			
Single pulse avalanche current		I <sub>AS</sub>	-16.5		
Single pulse avalanche energy	L = 0.1 mH	E <sub>AS</sub>	13.6	mJ	
	T <sub>C</sub> = 25 °C	D	5	w	
Maximum power dissipation	T <sub>C</sub> = 125 °C	P <sub>D</sub>	1.6		
Operating junction and storage temperature	range	T <sub>J</sub> , T <sub>stq</sub>	-55 to +175	°C	

THERMAL RESISTANCE RATINGS						
PARAMETER		SYMBOL	LIMIT	UNIT		
Junction-to-ambient	PCB mount <sup>b</sup>	R <sub>thJA</sub>	110	°C/W		
Junction-to-foot (drain)		R <sub>thJF</sub>	30	C/ W		

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$ 

b. When mounted on 1" square PCB (FR4 material)

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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static							1	
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \mu\text{A}$		-40	-	-	v	
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = -250 \ \mu A$		-1.5	-2.0	-2.5	v	
Gate-source leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 20 V$		-	-	± 100	nA	
Zero gate voltage drain current		$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V	-	-	-1		
	I <sub>DSS</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 125 °C	-	-	-50	μA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 175 °C	-	-	-150		
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	$V_{GS} = -10 V$	V <sub>DS</sub> = -5 V	-10	-	-	Α	
		$V_{GS} = -10 \text{ V}$	I <sub>D</sub> = -2.5 A	-	0.048	0.058	Ω	
Ducin actures on state registeres a	P	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -2.5 A, T <sub>J</sub> = 125 °C	-	0.075	-		
Drain-source on-state resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -2.5 A, T <sub>J</sub> = 175 °C	-	0.086	-		
		$V_{GS} = -4.5 V$	I <sub>D</sub> = -2 A	-	0.076	0.092		
Forward transconductance <sup>b</sup>	9 <sub>fs</sub>	V <sub>DS</sub> :	= -20 V, I <sub>D</sub> = -4 A	-	8	-	S	
Dynamic <sup>b</sup>					•			
Input capacitance	C <sub>iss</sub>		V <sub>DS</sub> = -20 V, f = 1 MHz	-	745	990	pF	
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$		-	134	180		
Reverse transfer capacitance	C <sub>rss</sub>			-	83	100		
Total gate charge <sup>c</sup>	Qg		V <sub>DS</sub> = -20 V, I <sub>D</sub> = -4 A	-	8.35	11.3	nC	
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>GS</sub> = -4.5 V		-	2.9	-		
Gate-drain charge <sup>c</sup>	Q <sub>gd</sub>			-	4.0	-		
Gate resistance	Rg	f = 1 MHz		2.6	5.7	7.9	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>	$V_{DD} = -20 \text{ V}, \text{ R}_{L} = 5 \Omega$ $\text{I}_{D} \cong -4 \text{ A}, \text{ V}_{\text{GEN}} = -10 \text{ V}, \text{ R}_{g} = 1 \Omega$		-	8	12	- ns	
Rise time <sup>c</sup>	t <sub>r</sub>			-	24	36		
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>			-	26	39		
Fall time <sup>c</sup>	t <sub>f</sub>			-	31	47		
Source-Drain Diode Ratings and Charac	teristics <sup>b</sup>							
Pulsed current <sup>a</sup>	I <sub>SM</sub>				-	-27	Α	
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = -1.6 A, V <sub>GS</sub> = 0 V		-	-0.8	-1.2	V	
Body diode reverse recovery time	t <sub>rr</sub>	-		-	24	48	ns	
Body diode reverse recovery charge	Q <sub>rr</sub>			-	23	46	nC	
Reverse recovery fall time	ta	I <sub>F</sub> = -3	A, di/dt = 100 A/µs	-	16	-		
Reverse recovery rise time	t <sub>b</sub>	1		-	8	-	ns	
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	-2.17	-	Α	

Notes

a. Pulse test; pulse width  $\leq 300~\mu s,~duty~cycle \leq 2~\%$ 

b. Guaranteed by design, not subject to production testing

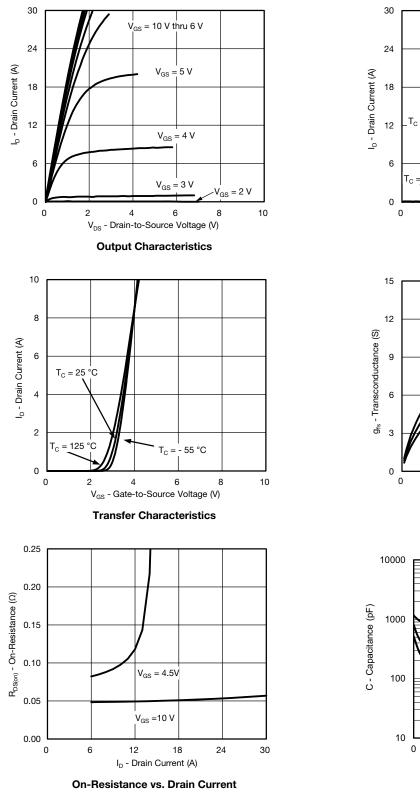
c. Independent of operating temperature

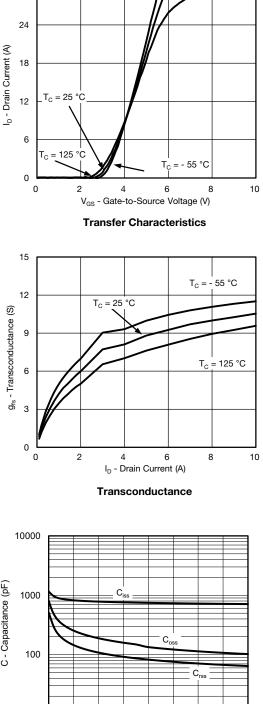
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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#### **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)





V<sub>DS</sub> - Drain-to-Source Voltage (V) Capacitance

30 35 40

15 20 25

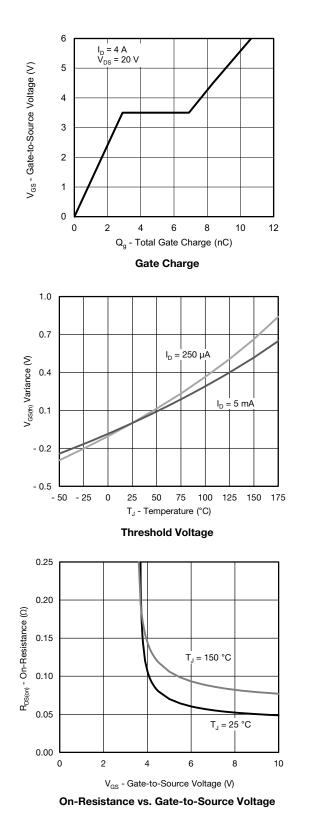
5 10

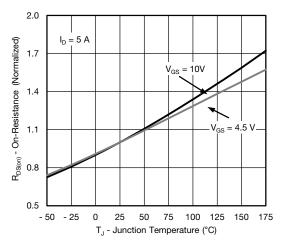


### SQ3419CEV

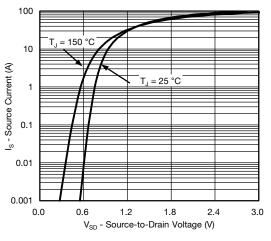
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#### **TYPICAL CHARACTERISTICS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

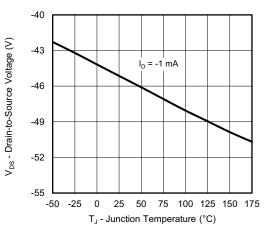




**On-Resistance vs. Junction Temperature** 



Source Drain Diode Forward Voltage



Drain Source Breakdown vs. Junction Temperature

S23-0496-Rev. A, 03-Jul-2023

4

Document Number: 62368

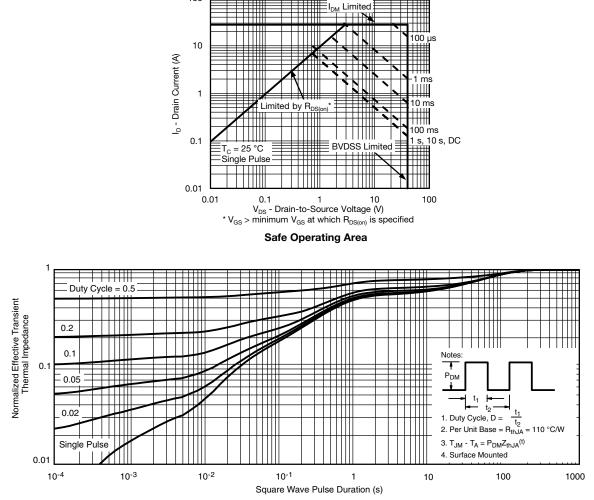
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#### **THERMAL RATINGS** ( $T_A = 25 \text{ °C}$ , unless otherwise noted)

100



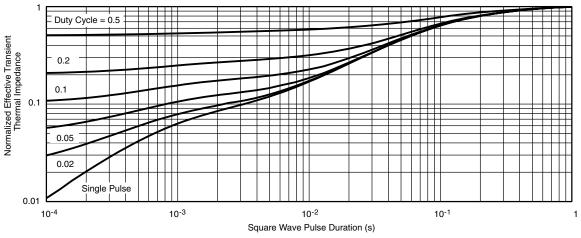
Normalized Thermal Transient Impedance, Junction-to-Ambient



### Vishay Siliconix

Document Number: 62368

#### THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Foot

#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?62368.



Package Information

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TSOP: 5/6-LEAD JEDEC Part Number: MO-193C









6-LEAD TSOP



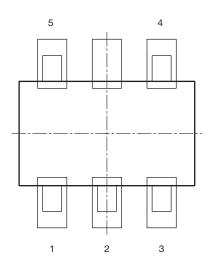
	MILLIMETERS			INCHES					
Dim	Min	Nom	Max	Min	Nom	Max			
Α	0.91	-	1.10	0.036	-	0.043			
<b>A</b> <sub>1</sub>	0.01	-	0.10	0.0004	-	0.004			
A <sub>2</sub>	0.90	-	1.00	0.035	0.038	0.039			
b	0.30	0.32	0.45	0.012	0.013	0.018			
С	0.10	0.15	0.20	0.004	0.006	0.008			
D	2.95	3.05	3.10	0.116	0.120	0.122			
Е	2.70	2.85	2.98	0.106	0.112	0.117			
E <sub>1</sub>	1.55	1.65	1.70	0.061	0.065	0.067			
е		0.95 BSC			0.0374 BSC				
<b>e</b> <sub>1</sub>	1.80	1.90	2.00	0.071	0.075	0.079			
L	0.32	-	0.50	0.012	-	0.020			
L <sub>1</sub>		0.60 Ref			0.024 Ref				
L <sub>2</sub>	0.25 BSC				0.010 BSC				
R	0.10	-	-	0.004	-	-			
θ	0°	4°	8°	0°	4°	8°			
$\theta_1$	7° Nom				7° Nom				
		ev. I, 18-Dec	c-06			ECN: C-06593-Rev. I, 18-Dec-06 DWG: 5540			

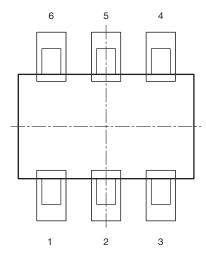
### **PAD** Pattern



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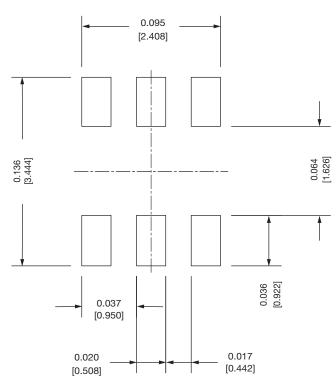
## **Recommended Land Pattern For TSOP-5L / TSOP-6L**





TSOP 5L





#### Note

• All dimensions are in inches (millimeter)

ECN: C22-0860-Rev. B, 24-Oct-2022	
DWG: 3010	



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Revision: 01-Jan-2024